

Abstract of the Disclosure

A semiconductor device includes source/drain regions, a gate pattern disposed on the semiconductor substrate between the source/drain regions, and L-shaped spacers that are used as masks in the forming of the source/drain regions. The L-shaped spacers each include a vertical portion covering a side wall of the gate pattern, and a lateral portion extending from the bottom of the vertical portion over the source/drain region. Support portions interposed between the L-shaped spacers and the gate pattern support the lateral portions of the L-shaped spacers such that an air gap is defined between at least the lateral portions of the L-shaped spacers and the source/drain regions. The air gap minimizes the parasitic capacitance associated with the gate electrode of the semiconductor device.